

HIGH-SPEED 32K x 16 DUAL-PORT STATIC RAM

Features True Dual-Ported memory cells which allow simultaneous external logic IDT7027 easily expands data bus width to 32 bits or more access of the same memory location using the Master/Slave select when cascading more than High-speed access one device Military: 25/35/55ns (max) ٠ $M/\overline{S} = V_{H}$ for \overline{BUSY} output flag on Master. - Industrial: 25ns (max.) M/S = VIL for BUSY input on Slave - Commercial: 20/25/35/55ns (max.) **Busy and Interrupt Flags** Low-power operation **On-chip port arbitration logic** - IDT7027S Full on-chip hardware support of semaphore signaling Active: 750mW (typ.) between ports Standby: 5mW (typ.) Fully asynchronous operation from either port - IDT7027L TTL-compatible, single 5V (±10%) power supply Active: 750mW (typ.) Available in 100-pin Thin Quad Flatpack (TQFP) and 108-pin Standby: 1mW (typ.) Ceramic Pin Grid Array (PGA) Separate upper-byte and lower-byte control for bus ٠ Industrial temperature range (-40°C to +85°C) is available matching capability. Dual chip enables allow for depth expansion without for selected speeds

Functional Block Diagram

R/WL R/WR UBL UBR CEOR CEOL CE1L CE1R ŌĒR OEL ĽΒ LBR Д I/O8-15R I/O 8-15L I/O I/O • Control Control I/O 0-7L I/O0-7R $\overline{\text{BUSY}}R^{(1,2)}$ 4 $\overline{\text{BUSY}}L^{(1,2)}$ 32Kx16 A14R A14L Address Address . MEMORY . ARRAY Decoder Decoder AOL AOR 7027 A14L 5 -5 A14R • . AOL S -S AOR ARBITRATION CEOL S INTERRUPT SEMAPHORE CE1L S S CE1R I OGIC OEL ¢ -∫ OEr R/WL 5 SR/WR SEM **SEM**R $\overline{\mathsf{INT}}\,\mathsf{L}^{(2)}$ $\overline{INT}R^{(2)}$ $M/\overline{S}^{(2)}$ 3199 drw 01

NOTES:

1. BUSY is an input as a Slave (M/S=VIL) and an output as a Master (M/S=VIH).

2. BUSY and INT are non-tri-state totem-pole outputs (push-pull).

MAY 2000

Military, Industrial and Commercial Temperature Ranges

Description

The IDT7027 is a high-speed 32K x 16 Dual-Port Static RAM, designed to be used as a stand-alone 512K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit-or-more word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

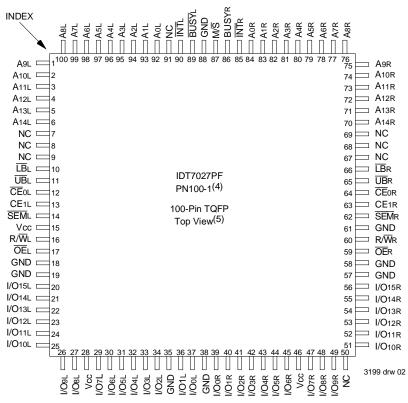
The device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (CE0 and CE1) permits the on-chip

circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 750mW of power. The IDT7027 is packaged in a 100-pin Thin Quad Flatpack (TQFP) and a 108-pin ceramic Pin Grid Array (PGA).

Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

Pin Configurations^(1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Configurations^(1,2,3) (con't.)

				=0							
A10R	A11R	A14R	NC	UB _R	SEM _R	GND	GND	NC			54 NC
84 A7R	83 A8R	78 A13R	76 NC	73 TBR	70 CE1R	67 R/WR	64 GND	61 I/O14R	59 I/O12R	56 I/O9R	⁵³ NC
87 A4R	86 A5R	82 A9R	79 A12R	75 NC	71 CEOR	66 OER	62 I/O15R	58 I/O11R	55 NC	51 I/O8R	50 I/O7R
90 A1R	88 A3R	85 A6R					1		52 NC	49 Vcc	47 I/O5R
92 INT _R	91 Aor	89 A2R							48 I/O6R	46 I/O4R	45 І/Озг
95 GND	94 M/S	93 BUSYR							44 I/O2R	43 I/O1R	42 I/Oor
96 BUSYL	97 INTL	98 NC			108-Pi		39 I/O1L	40 I/Ool	41 GND		
99 Aol	100 A1L	102 Азь			Top V	IEW ⁽⁵⁾			35 I/O4L	37 I/O2L	38 GND
101 A2L	103 A4L	106 A7L							31 Vcc	34 I/O5L	36 I/O3L
104 A5L	105 A6L	1 A10L	4 A13L	⁸ NC	12 CE1L	17 GND	21 I/O14L	25 I/O10L	28 NC	32 I/O7L	33 I/O6L
107 A8L	2 A11L	5 A14L	7 NC	10 UBL	13 SEML	16 OEL	19 GND	22 I/O13L	24 I/O11L	29 NC	30 I/O8L
108 A9L	3 A12L	6 NC	9 LBL	11 CE _{0L}	14 Vcc	15 R/WL	18 NC	20 I/O15L	23 I/O12L	26 I/O9L	27 NC
A	В	С	D	E	F	G	Н	J	ĸ	L	М
	84 A7R 87 A4R 90 A1R 92 INTR 95 GND 96 BUSYL 99 A0L 101 A2L 104 A5L 107 A8L 108 A9L	A10R A11R 84 83 A7R A8R 87 86 A4R A5R 90 88 A1R A3R 92 91 INTR 94 95 94 96 97 BUSYL 97 BUSYL 100 A0L A1L 101 103 A2L A4L 104 A6L 107 2 A8L A11L 108 3 A9L A12L	A10R A11R A14R 84 83 78 A7R A8R A13R 87 86 82 A4R A5R A9R 90 88 85 A1R A3R A6R 92 91 89 INTR 94 93 95 94 93 96 97 98 BUSYL 97 98 BUSYL 100 102 A0L A1L A3L 101 103 106 A2L A4L A7L 104 A6L A10L 107 2 5 A8L A11L A14L 108 3 6 A9L A12L NC	A10R A11R A14R NC 84 83 78 A13R 76 A7R 86 82 79 A12R 87 86 82 79 A12R 90 88 85 A9R A12R 90 88 85 A6R 91 92 91 A0R B2R 95 94 93 BUSYR 96 97 98 BUSYR 96 97 98 NC 99 100 102 A0L A1L A3L 101 103 106 A2L A4L A7L 104 A5L A6L A10L 104 A5L A6L A14L 107 2 5 7 A8L A11L A14L NC 108 3 6 9 IEL	A10R A11R A14R NC UBR 84 83 78 76 73 IBR 87 86 82 79 75 NC 90 88 85 A6R A6R 79 NC 90 88 85 A6R 92 79 NC NC 90 88 85 A6R 92 91 89 A2R 93 95 94 93 BUSYR 97 NC 99 100 102 A0L A1L A3L A7L A1L A3L NC 99 100 102 A4L A7L NC NC 99 100 102 A4L A7L NC NC 101 103 106 A2L A4L A7L NC 104 A5L A6L A10L A13L NC NC 107 2 5	A10R A11R A14R NC UBR SEMR 84 83 78 76 73 70 CE1R 87 86 82 79 75 71 CE0R 90 88 85 A13R A6R A12R NC CE0R 90 88 85 A1R A3R A6R A12R NC CE0R 90 88 85 A1R A3R A6R A12R NC CE0R 90 88 85 A6R A12R NC CE0R CE0R 92 91 BOR A2R A1R A3R A6R A1R A0R A1D G108 95 94 93 BUSYR BUSYR IDT70 G108 108-Pi TOP V 99 100 102 A1L A3L A108-Pi TOP V 101 103 106 A1L A13L NC CE1L </td <td>A10R A11R A14R NC UBR SEMR GND 84 83 78 A13R 76 73 70 67 87 86 82 79 A12R NC IEBR 71 66 90 88 85 A1R A6R A6R A6R 90 88 85 A1R A6R A6R A6R 92 91 89 A2R A6R A6R A6R 92 94 93 BUSYR IDT7027G G108-1(4) 95 94 93 BUSYR IDT8027(14) 108-Pin PGA 99 100 102 A1L A3L 108-Pin PGA 101 103 106 A2L A4L A7L 108-Pin View⁽⁵⁾ 104 A11L A3L A12L A6L A10L A13L NC ICE1L GND 107 2 5 7 10 13</td> <td>A10R A11R A14R NC UBR SEMR GND GND 84 83 78 A13R 76 73 70 67 64 GND 87 86 82 79 A12R 75 71 66 62 I/O15R 90 88 85 A1R A3R A6R A2R A3R A6R A2R A12R NC 70 67 64 GND 90 88 85 A3R A6R A2R A1R A3R A6R A1L A1R A1R A2R A1R A1R A2R A1R A1R</td> <td>A10R A11R A14R NC UBR SEMR GND GND NC 84 83 78 A13R 76 73 70 67 64 61 87 86 82 79 75 71 66 62 58 A4R A5R A9R A12R NC ÏER NC ICEOR OER 62 58 90 88 85 A6R A6R A9R A12R NC ICEOR OER 1/O15R I/O11R 90 88 85 A6R A6R A2R IDT7027G G108-1(4) 95 94 93 BUSYR PROC IDT7027G G108-1(4) 96 97 NC 108 PINTE PROC IDT8 IO8-PIN PGA 99 100 102 A0L A1L A3L NC ICE1L GND I/O14L I/O10L 104 A6L A1</td> <td>A10R A11R A14R NC UBR SEMR GND GND NC I/O13R 84 83 78 A13R 76 73 70 67 64 61 59 A7R A8R A13R NC IBR CE1R R/WR GND I/O14R I/O12R 87 86 82 79 75 71 66 62 58 55 A4R A5R A9R A12R NC ICER OER 67 66 62 58 55 NC 90 88 85 A1R A3R A6R 9 NC IDT7027G IO8-Pin PGA NC 48 I/O1L 99 100 102 108-Pin PGA 108-Pin View(5) 39 I/O1L 35 I/O1L 31</td> <td>$\begin{array}{ c c c c c c c c c c c c c c c c c c c$</td>	A10R A11R A14R NC UBR SEMR GND 84 83 78 A13R 76 73 70 67 87 86 82 79 A12R NC IEBR 71 66 90 88 85 A1R A6R A6R A6R 90 88 85 A1R A6R A6R A6R 92 91 89 A2R A6R A6R A6R 92 94 93 BUSYR IDT7027G G108-1(4) 95 94 93 BUSYR IDT8027(14) 108-Pin PGA 99 100 102 A1L A3L 108-Pin PGA 101 103 106 A2L A4L A7L 108-Pin View ⁽⁵⁾ 104 A11L A3L A12L A6L A10L A13L NC ICE1L GND 107 2 5 7 10 13	A10R A11R A14R NC UBR SEMR GND GND 84 83 78 A13R 76 73 70 67 64 GND 87 86 82 79 A12R 75 71 66 62 I/O15R 90 88 85 A1R A3R A6R A2R A3R A6R A2R A12R NC 70 67 64 GND 90 88 85 A3R A6R A2R A1R A3R A6R A1L A1R A1R A2R A1R A1R A2R A1R A1R	A10R A11R A14R NC UBR SEMR GND GND NC 84 83 78 A13R 76 73 70 67 64 61 87 86 82 79 75 71 66 62 58 A4R A5R A9R A12R NC ÏER NC ICEOR OER 62 58 90 88 85 A6R A6R A9R A12R NC ICEOR OER 1/O15R I/O11R 90 88 85 A6R A6R A2R IDT7027G G108-1(4) 95 94 93 BUSYR PROC IDT7027G G108-1(4) 96 97 NC 108 PINTE PROC IDT8 IO8-PIN PGA 99 100 102 A0L A1L A3L NC ICE1L GND I/O14L I/O10L 104 A6L A1	A10R A11R A14R NC UBR SEMR GND GND NC I/O13R 84 83 78 A13R 76 73 70 67 64 61 59 A7R A8R A13R NC IBR CE1R R/WR GND I/O14R I/O12R 87 86 82 79 75 71 66 62 58 55 A4R A5R A9R A12R NC ICER OER 67 66 62 58 55 NC 90 88 85 A1R A3R A6R 9 NC IDT7027G IO8-Pin PGA NC 48 I/O1L 99 100 102 108-Pin PGA 108-Pin View(5) 39 I/O1L 35 I/O1L 31	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$

NOTES:

- All Vcc pins must be connected to power supply.
 All GND pins must be connected to ground supply.
 Package body is approximately 1.21 in x 1.21 in x .16 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
CEOL, CE1L	\overline{CE} OR, CE1R	Chip Enables
R/WL	R/WR	Read/Write Enable
ŌĒL	ŌĒr	Output Enable
Aol - A14L	Aor - A14r	Address
I/Ool - I/O15L	I/Oor - I/O15r	Data Input/Output
SEML	SEMR	Semaphore Enable
ŪBL	ŪBR	Upper Byte Select
L BL	LB R	Lower Byte Select
ĪNTL	ĪNTr	Interrupt Flag
BUSYL	BUSYR	Busy Flag
Μ	I/S	Master or Slave Select
V	сс	Power
G	ND	Ground

Truth Table I – Chip Enable

CE	C E0	CE1	Mode
	Vı∟	Viн	Port Selected (TTL Active)
L	<u><</u> 0.2V	Port Selected (CMOS Active)	
	Vн	Х	Port Deselected (TTL Inactive)
	Х	Vil	Port Deselected (TTL Inactive)
Н	<u>≥</u> Vcc -0.2V	Х	Port Deselected (CMOS Inactive)
	Х	<u>≤</u> 0.2V	Port Deselected (CMOS Inactive)

NOTES:

1. Chip Enable references are shown above with the actual \overline{CE}_0 and CE_1 levels, \overline{CE} is a reference only.

2. Port "A" and "B" references are located where \overline{CE} is used.

3. "H" = VIH and "L" = VIL.

Truth Table II – Non-Contention Read/Write Control

		Inpu	uts ⁽¹⁾			Out	puts	
CE ⁽²⁾	R/₩	ŌĒ	UB	ΓB	SEM	I/O8-15	I/O0-7	Mode
Н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
Х	Х	Х	Н	Н	Н	High-Z	High-Z	Both Bytes Deselected
L	L	Х	L	Н	Н	DATAIN	High-Z	Write to Upper Byte Only
L	L	Х	Н	L	Н	High-Z	DATAIN	Write to Lower Byte Only
L	L	Х	L	L	Н	DATAIN	DATAIN	Write to Both Bytes
L	Н	L	L	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	Н	L	Н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	Н	L	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. Aol — A14L \neq Aor — A14R.

2. Refer to Chip Enable Truth Table.

Truth Table III – Semaphore Read/Write Control

		Inpu	uts ⁽¹⁾			Out	puts	
CE ⁽²⁾	R∕₩	ŌĒ	ŪB	LB	SEM	I/O8-15	I/O0-7	Mode
Н	Н	L	Х	Х	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Н	\uparrow	Х	Х	Х	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
Х	Ŷ	Х	Н	Н	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L	Х	L			Not Allowed
L	Х	Х	Х	L	L			Not Allowed

NOTES:

1. There are eight semaphore flags written to via I/Oo and read from all the I/Os (I/Oo –I/O15). These eight semaphore flags are addressed by Ao-A2. 2. Refer to Chip Enable Truth Table.

3199 tbl 04

3199 tbl 03

Military, Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings^(1,3)

Symbol	Rating	Commercial & Industrial	Military	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	-65 to +135	٥C
Tstg	Storage Temperature	-65 to +150	-65 to +150	٥C
Ιουτ	DC Output Current	50	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	۷
GND	Ground	0	0	0	V
V⊪	Input High Voltage	2.2		6.0 ⁽²⁾	۷
Vil	Input Low Voltage	-0.5 ⁽¹⁾		0.8	۷
					3199 tbl 07

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to+125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%
			3199 tbl 06

NOTES:

3199 tbl 05

1. This is the parameter TA. This is the "instant on" case temperature.

2. Industrial temperature: for other speeds packages and powers, contact your sales office.

Capacitance⁽¹⁾

(TA = +25°C, f = 1.0mhz) TQFP ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	Vin = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF
				3199 tbl 08

NOTES:

- 1. This parameter is determined by device characterization but is not production tested.
- 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			7027S		702		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, V IN = 0V to Vcc	_	10		5	μA
LO	Output Leakage Current	$\overline{CE} = V_{H}$, Vout = 0V to Vcc	-	10		5	μA
Vol	Output Low Voltage	Iol = 4mA	-	0.4	-	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	V

NOTE:

1. At Vcc \leq 2.0V, input leakages are undefined.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,6,7) (Vcc = 5.0V ± 10%)

						7027X20 Com'l Only		7027X25 Com'l, Ind & Military		'X35 n'I & tary	7027X55 Com'l & Military		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	<u>CE</u> = V _{IL} , Outputs Disabled SEM = Vi⊢ f = fMax ⁽³⁾	COM'L	S L	185 185	325 285	180 170	305 265	160 160	295 255	150 150	270 230	mA
	(DUIT POILS ACUVE)	$1 = IMAX^{e_j}$	MIL & IND	S L			170 170	345 305	160 160	335 295	150 150	310 270	
ISB1	Standby Current (Both Ports - TTL Level	$\overline{\underline{CEL}} = \overline{\underline{CER}} = \underline{VH}$ $\overline{\underline{SEMR}} = \overline{\underline{SEML}} = \underline{VH}$	COM'L	S L	55 55	90 70	40 40	85 60	30 30	85 60	20 20	85 60	mA
	linp uts)	$f = f_{MAX}^{(3)}$	MIL & IND	S L			40 40	100 80	30 30	100 80	20 20	100 80	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{*}A^{*} = VIL \text{ and } \overline{CE}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled,	COM'L	S L	120 120	215 185	105 105	200 170	95 95	185 155	85 85	165 135	mA
	inpuis)	$\frac{f=f_{MA}x^{(3)}}{SEM_{R}} = \overline{SEM}_{L} = V_{H}$	MIL & IND	S L			105 105	230 200	95 95	215 185	85 85	195 165	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports \overline{CE}_{L} and $\overline{CE}_{R} \ge Vcc - 0.2V$ VN > Vcc - 0.2V or	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Level liipuis)	$\frac{V_{IN} \leq 0.2V, f = 0^{(4)}}{SEM_R = SEM_L \geq V_{CC} - 0.2V}$	MIL & IND	S L			1.0 0.2	30 10	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\label{eq:cellson} \begin{array}{l} \overline{CE}^{*} \mathbb{A}^{*} &\leq 0.2V \text{ and} \\ \overline{CE}^{*} \mathbb{B}^{*} &\geq V \mathbb{CC} - 0.2V^{(5)} \\ \overline{SEMR} &= \overline{SEML} \geq V \mathbb{CC} - 0.2V \end{array}$	COM'L	S L	115 115	190 160	100 100	170 145	90 90	160 135	80 80	135 110	mA
		$\begin{array}{l} V \hbox{$\mathbb{N} \geq Vcc - 0.2V$ or} \\ V \hbox{$\mathbb{N} \leq 0.2V$, Active Port Outputs$} \\ Disabled, f = fmax^{(3)} \end{array}$	MIL & IND	S L			100 100	200 175	90 90	190 165	80 80	175 150	

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

2. Vcc = 5V, TA = $+25^{\circ}$ C, and are not production tested. Icccc = 120mA (Typ.)

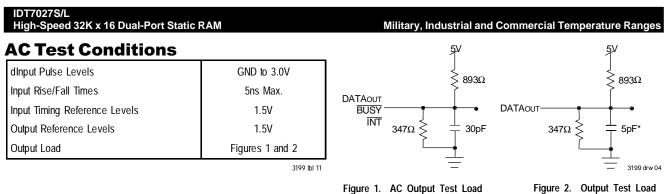
3. At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/ trc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6. Refer to Chip Enable Truth Table.

7. Industrial temperature: for other speeds, packages and powers contact your sales office.



(for tLz, tHz, twz, tow) *Including scope and jig.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Ranges^(4,6)

			7027X20 Com'l Only		7027X25 Com'l, Ind. & Military		7X35 n'I& itary	7027X55 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCL	E	-								
trc	Read Cycle Time	20		25		35		55		ns
taa	Address Access Time		20	-	25		35		55	ns
t ACE	Chip Enable Access Time ⁽³⁾		20	-	25		35		55	ns
t ABE	Byte Enable Access Time ⁽³⁾		20		25		35		55	ns
t AOE	Output Enable Access Time		12	-	13		20		30	ns
tон	Output Hold from Address Change	3		3		3		3		ns
۱LZ	Output Low-Z Time ^(1,2)	3	_	3	_	3		3		ns
tHZ	Output High-Z Time ^(1,2)		12	-	15		15		25	ns
tPU	Chip Enable to Power Up Time ^(2,5)	0	_	0	_	0		0		ns
tpd	Chip Disable to Power Down Time ^(2,5)		20		25		35		50	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	10		12		15	_	15		ns
tsaa	Semaphore Address Access Time		20		25		35		55	ns

3199 tbl 12

NOTES:.

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

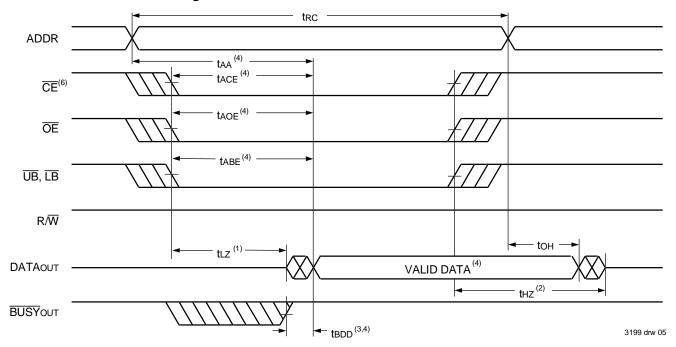
2. This parameter is guaranteed by device characterization, but is not production tested.

3. To access RAM, \overrightarrow{CE} = VIL and \overrightarrow{SEM} = VIH. To access semaphore, \overrightarrow{CE} = VIH and \overrightarrow{SEM} = VIL.

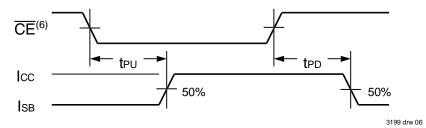
4. 'X' in part numbers indicates power rating (S or L).

5. Refer to Chip Enable Truth Table.

Waveform of Read Cycles⁽⁵⁾



Timing of Power-Up Power-Down



- 1. Timing depends on which signal is asserted last, \overline{CE} , \overline{OE} , \overline{LB} , or \overline{UB} .
- 2. Timing depends on which signal is de-asserted first \overline{CE} , \overline{OE} , \overline{LB} , or \overline{UB} .
- 3. tbdb delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last taoe, tace, tace, tac or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$
- 6. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage^(5,6)

	ol Parameter		7X20 Only	Com	7027X25 Com'l, Ind & Military		7027X35 Com'l & Military		7027X55 Com'l & Military	
Symbol			Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	Unit
WRITE CY	CLE			-	-			-		-
twc	Write Cycle Time	20		25		35		55		ns
tew	Chip Enable to End-of-Write ⁽³⁾	15		20		30		45		ns
taw	Address Valid to End-of-Write	15	_	20		30		45		ns
tas	Address Set-up Time ⁽³⁾	0	-	0		0		0		ns
₩P	Write Pulse Width	15		20		25		40		ns
twr	Write Recovery Time	0		0		0		0		ns
tow	Data Valid to End-of-Write	15		15		15		30		ns
tHZ	Output High-Z Time ^(1,2)	_	12	_	15		15		25	ns
tDH	Data Hold Time ⁽⁴⁾	0		0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)	—	12	_	15	_	15	_	25	ns
tow	Output Active from End-of-Write ^(1,2,4)	0		0		0		0		ns
tswrd	SEM Flag Write to Read Time	5		5		5		5		ns
tsps	SEM Flag Contention Window	5		5		5		5		ns

NOTES:

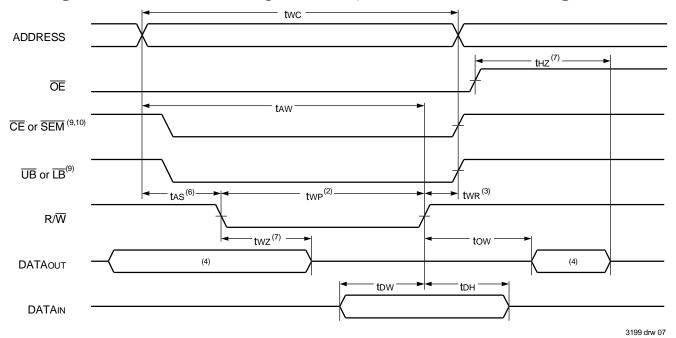
1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

 This parameter is guaranteed by device characterization, but is not production tested.
 To access RAM CE= VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. Either condition must be valid for the entire tew time. Refer to Chip Enable Truth Table.

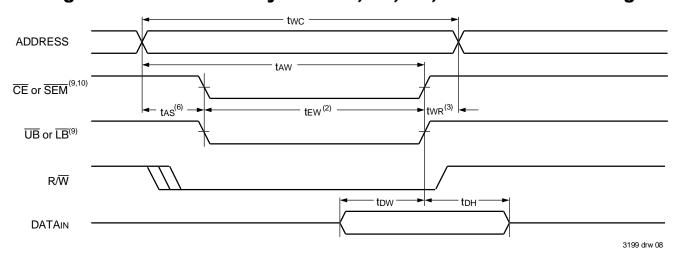
4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

5. 'X' in part numbers indicates power rating (S or L).

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,5,8)

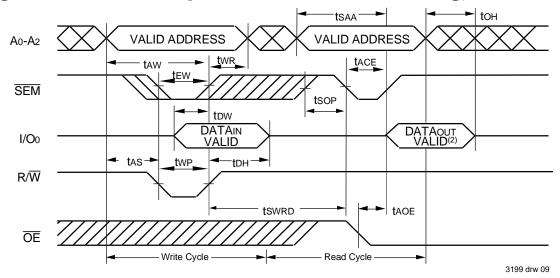


Timing Waveform of Write Cycle No. 2, \overline{CE} , \overline{UB} , \overline{LB} Controlled Timing^(1,5)



- 1. R/\overline{W} or \overline{CE} or \overline{UB} and $\overline{LB} = V_{IH}$ during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a CE = VIL and a R/W = VIL for memory array writing cycle.
- 3. twr is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM = VIL transition occurs simultaneously with or after the RW = VIL transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} = VIL during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If \overline{OE} = VIH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, \overline{CE} = VIL and \overline{SEM} = VIH. To access semaphore, \overline{CE} = VIH and \overline{SEM} = VIL. tew must be met for either condition.
- 10. Refer to Chip Enable Truth Table.

Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾

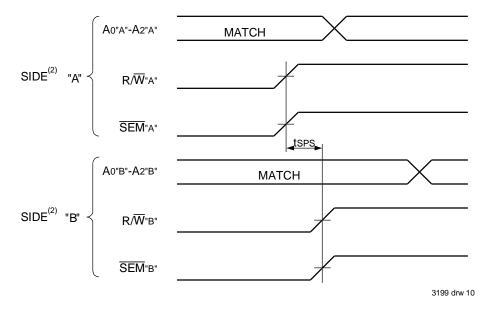


NOTES:

1. \overline{CE} = VIH or \overline{UB} and \overline{LB} = VIH for the duration of the above timing (both write and read cycle), refer to Chip Enable Truth Table.

2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



- 1. DOR = DOL = VIL, $\overline{CE}R = \overline{CE}L = VIH$, or both $\overline{UB} \& \overline{LB} = VIH$ (refer to Chip Enable Truth Table).
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from RMT ar or SEM ar going HIGH to RMT br or SEM br going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will be granted the semaphore flag.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(6,7)

			7027X20 Com'l Only		7027X25 Com'l, Ind. & Military		7027X35 Com'l & Military		7027X55 Com'l & Military	
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	Unit
	NG (M/S=Vih)									
t BAA	BUSY Access Time from Address Match		20		20	-	20	-	45	ns
t BDA	BUSY Disable Time from Address Not Matched		20		20	-	20	-	40	ns
t BAC	BUSY Access Time from Chip Enable Low		20		20	-	20	-	40	ns
tBDC	BUSY Access Time from Chip Enable High		17		17	_	20		35	ns
t APS	Arbitration Priority Set-up Time ⁽²⁾	5		5		5		5		ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		30		30		35		40	ns
twн	Write Hold After $\overline{\text{BUSY}}^{(5)}$	15		17		25		25		ns
	NG (M/S=VIL)									
twв	BUSY Input to Write ⁽⁴⁾	0		0		0		0		ns
twн	Write Hold After $\overline{\text{BUSY}}^{(5)}$	15		17		25		25		ns
PORT-TO-P	ORT DELAY TIMING	-			-					
twdd	Write Pulse to Data Delay ⁽¹⁾		45		50		60		80	ns
tDDD	Write Data Valid to Read Data Delay ⁽¹⁾		30		35		45	-	65	ns
	-	-					-		- 3	3199 tbl 1

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VIH)".

2. To ensure that the earlier of the two ports wins.

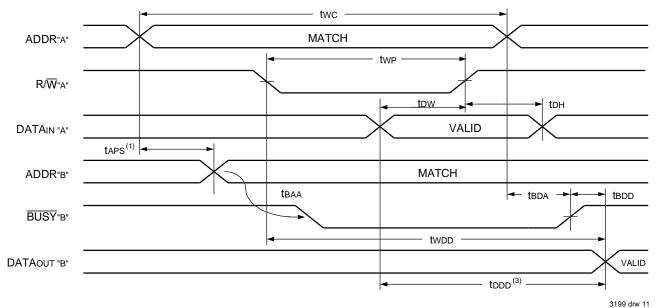
3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual), or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

6. 'X' in part numbers indicates power rating (S or L).

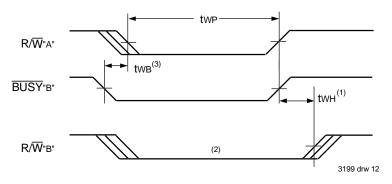
Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIH)^(2,4,5)



NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = VIL$ (slave).
- 2. $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}$ (refer to Chip Enable Truth Table).
- 3. \overline{OE} = VIL for the reading port.
- 4. If M/S = VIL (slave), BUSY is an input. Then for this example BUSY A* = VIH and BUSY B* input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

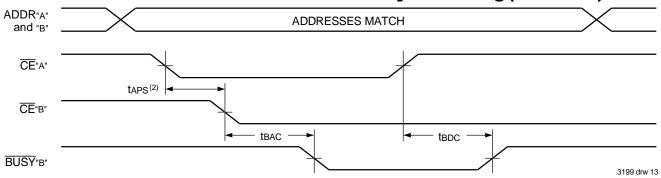
Timing Waveform of Write with $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIL)



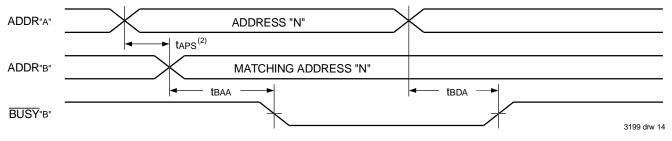
- 1. twn must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the "Slave" version.

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Waveform of **BUSY** Arbitration Controlled by \overline{CE} Timing (M/ \overline{S} = VIH)^(1,3)



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing $(M/\overline{S} = VIH)^{(1)}$



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

3. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,2)

		7027X20 Com'l Only		7027X25 Com'l, Ind & Military		7027X35 Com'l & Military		7027X55 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Мах.	Unit
INTERRUPT	TIMING	2	-	-	-	-	-	-		-
tas	Address Set-up Time	0		0		0		0		ns
twr	Write Recovery Time	0		0		0		0		ns
tins	Interrupt Set Time		20		20		25		40	ns
tinr	Interrupt Reset Time		20		20		25		40	ns
		•	•			•				3199 tbl 15

NOTES:

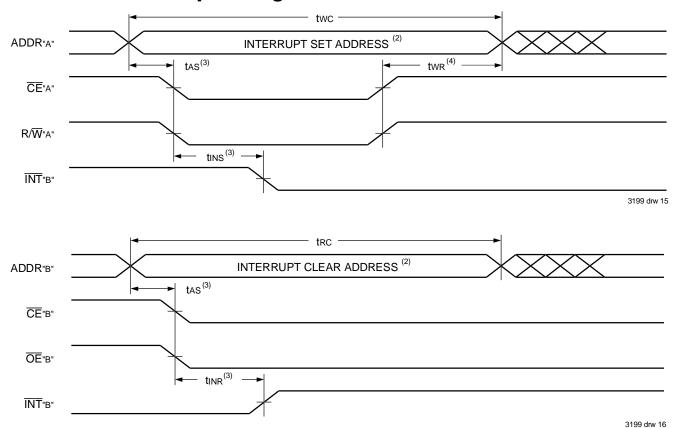
1. 'X' in part numbers indicates power rating (S or L).

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Waveform of Interrupt Timing^(1,5)

High-Speed 32K x 16 Dual-Port Static RAM

IDT7027S/L



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. See the Interrupt Truth Table IV.

- 3. Timing depends on which enable signal (\overline{CE} or R/ \overline{W}) is asserted last.
- 4. Timing depends on which enable signal $\overline{(CE}$ or R/\overline{W}) is de-asserted first.
- 5. Refer to Chip Enable Truth Table.

Left Port										
R/₩L	CE∟	OEL	A14L-A0L	ĪNTL	R/WR	CER	OE R	A14R-A0R	ĪNTR	Function
L	L	Х	7FFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	7FFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FFE	Х	Set Left INTL Flag
Х	L	L	7FFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag
										3199 th 16

Truth Table IV — Interrupt Flag^(1,4)

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = V_{IH}$.

2. If $\overline{\text{BUSY}}_{L} = V_{IL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = \text{VIL}$, then no change.

4. Refer to Chip Enable Truth Table.

Truth Table V — Address Bus Arbitration⁽⁴⁾

	In	puts	Out	puts	
Ē	ĒĒR	Aol-A14L Aor-A14r	BUSYL ⁽¹⁾	BUSY _{R⁽¹⁾}	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

3199 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT7027 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

 "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of the actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of the actual logic level on the pin.

4. Refer to Chip Enable Truth Table.

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7027.

2. There are eight semaphore flags written to via I/O0 and read from all the I/O's (I/O0-I/O15). These eight semaphores are addressed by Ao-A2.

3. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$, to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT7027 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7027 has an automatic power down feature controlled by \overline{CE}_0 and CE1. The \overline{CE}_0 and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = VIH$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag

 (\overline{INTL}) is asserted when the right port writes to memory location 7FFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per Truth Table IV. The left port clears the interrupt through access of address location 7FFE when $\overline{CEL} = \overline{OEL} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interruptflag (\overline{INTR}) is asserted when the left port writes to memory location 7FFF (HEX) and to clear the interruptflag (\overline{INTR}), the right port must read the memory location 7FFF. The message (16 bits) at 7FFE or 7FFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations 7FFE and 7FFF are not used as mail-boxes by ignoring the interrupt, but as part of the random access memory. Refer to Truth Table IV for the interrupt operation.

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Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of busy logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW.

The BUSY outputs on the IDT7027 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

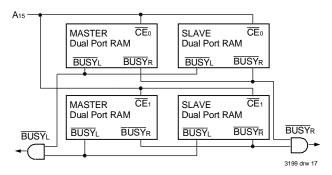


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7027 RAMs.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT7027 RAM array in width while using \overline{BUSY} logic, one master part is used to decide which side of the RAM array will receive a \overline{BUSY} indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the \overline{BUSY} signal as a write inhibit signal. Thus on the IDT7027 RAM the \overline{BUSY} pin is an output if the part is used as a Master (M/S pin = VIH), and the \overline{BUSY} pin is an input if the part used as a Slave (M/S pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating $\overline{\text{BUSY}}$ on one side of the array and another master indicating $\overline{\text{BUSY}}$ on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with either the R/\overline{W} signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT7027 is a fast Dual-Port 32K x 16 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port SRAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port SRAM or any other shared resource.

The Dual-Port SRAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port SRAM. These devices have an automatic power-down feature controlled by \overline{CE} the Dual-Port SRAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table II where \overline{CE} and $\overline{SEM} = VIH$.

Systems which can best use the IDT7027 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7027's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7027 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port SRAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to

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perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active low. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

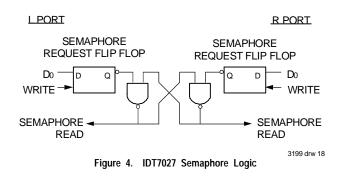
The eight semaphore flags reside within the IDT7027 in a separate memory space from the Dual-Port SRAM. This address space is accessed by placing a low input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{OE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0–A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Dois used. If a LOW level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table VI). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (\overline{SEM} or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Truth Table VI). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the



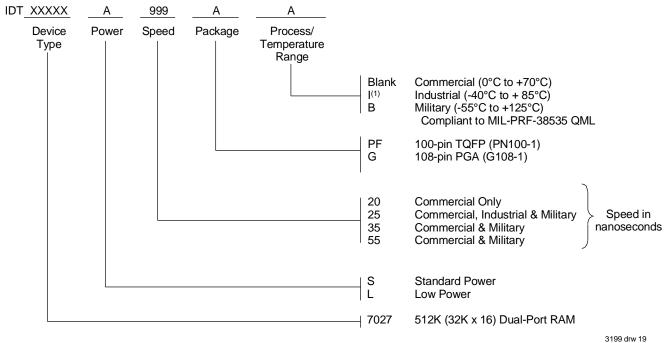
semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

Ordering Information



NOTE:

1. Industrial temperature range is available on selected TQFP packages in standard power. For other speeds, packages and powers contact your sales office.

Datasheet Document History

1/15/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Pages 2 and 3 Added additional notes to pin configurations
5/19/99:	Pages 4 and 16 Fixed typographical errors
6/3/99:	Changed drawing format
	Page 1 Corrected DSC number
11/10/99:	Replaced IDT logo
5/22/00:	Page 5 Increased storage temperature parameter
	Clarified TA parameter
	Page 6 DC Electrical parameters-changed wording from "open" to "disabled"
	Changed ±200mV to 0mV in notes



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